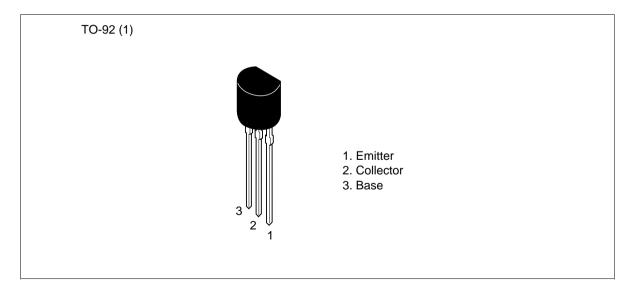
Silicon PNP Epitaxial

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Application

- Low frequency low noise amplifier
- Complementary pair with 2SC458 (LG) and 2SC2310

Outline





Absolute Maximum Ratings (Ta = 25° C)

Item	Symbol	2SA1031	2SA1032	Unit
Collector to base voltage	V _{CBO}	-30	-55	V
Collector to emitter voltage	V _{CEO}	-30	-50	V
Emitter to base voltage	V _{EBO}	-5	-5	V
Collector current	Ι _c	-100	-100	mA
Emitter current	Ι _Ε	100	100	mA
Collector power dissipation	Pc	300	300	mW
Junction temperature	Tj	150	150	°C
Storage temperature	Tstg	-55 to +150	-55 to +150	°C

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Electrical Characteristics (Ta = 25°C)

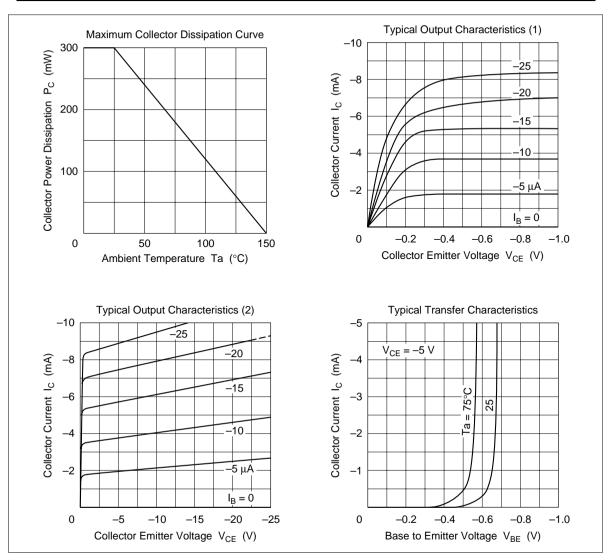
2SA1032

100 to 200

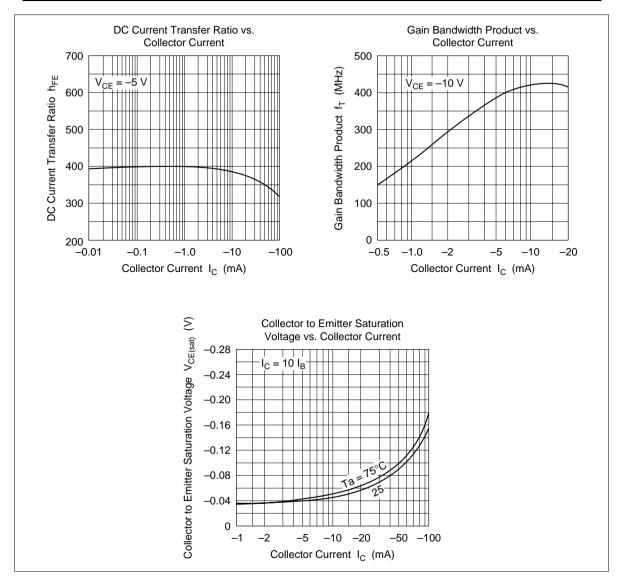
160 to 320

_

		2SA1	031		2SA1	2SA1032			
ltem	Symbol	Min	Тур	Мах	Min	Тур	Мах	Unit	Test conditions
Collector to base breakdown voltage	$V_{\rm (BR)CBO}$	-30	_	_	-55	_	_	V	$I_{c} = -10 \ \mu A, I_{E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-30	_	_	-50	_	_	V	$I_c = -1 \text{ mA}, \text{ R}_{BE} = \infty$
Emitter to base breakdown voltage	$V_{\rm (BR)EBO}$	-5	—	_	-5	_	—	V	$I_{\rm E} = -10 \ \mu A, \ I_{\rm C} = 0$
Collector cutoff current	I _{CBO}		_	-0.5		_	-0.5	μΑ	$V_{\rm CB} = -18 \text{ V}, I_{\rm E} = 0$
Emitter cutoff current	I _{EBO}			-0.5			-0.5	μΑ	$V_{EB} = -2 V, I_{C} = 0$
DC current trnsfer ratio	h_{FE}^{*1}	100	_	500	100	—	320		$V_{ce} = -12 V,$ $I_c = -2 mA$
Base to emitter voltage	V_{BE}	—	—	-0.8	_		-0.8	V	$V_{ce} = -12 V,$ $I_{c} = -2 mA$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	—	—	-0.2	_		-0.2	V	$I_{c} = -10 \text{ mA},$ $I_{B} = -1 \text{ mA}$
Gain bandwidth product	f _T	200	280	—	200	280	—	MHz	$V_{ce} = -12 V,$ $I_c = -2 mA$
Collector output capacitance	Cob	—	3.3	4.0	_	3.3	4.0	pF	$V_{CB} = -10 \text{ V}, \text{ I}_{E} = 0,$ f = 1 MHz
Noise figure	NF	_	_	5	_	_	5	dB	$V_{cE} = -6 V,$ $I_c = -0.1 mA,$ $R_g = 500 \Omega,$ f = 120 Hz
Note: 1. The 2SA1031 and 2SA1032 are grouped by h _{FE} as follows.									
В	С		D						
2SA1031 100 to 20	0 160 t	o 320	250 t	to 500					

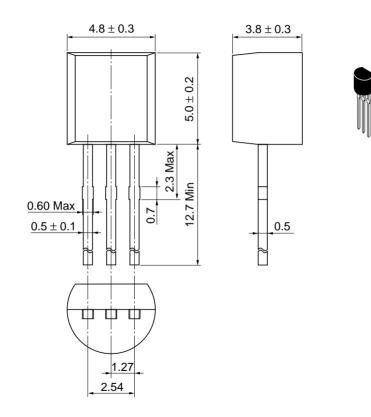


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Hitachi Code	TO-92 (1)
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	0.25 g

Cautions

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Semiconductor & Integrated Circuits. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109 NorthAmerica URL http:semiconductor.hitachi.com/ http://www.hitachi-eu.com/hel/ecg Europe http://www.has.hitachi.com.sg/grp3/sicd/index.htm http://www.hitachi.com.tw/E/Product/SICD_Frame.htm Asia (Singapore) Asia (Taiwan) Asia (HongKong) http://www.hitachi.com.hk/eng/bo/grp3/index.htm http://www.hitachi.co.jp/Sicd/indx.htm Japan For further information write to: Hitachi Semiconductor Hitachi Europe GmbH Hitachi Asia Pte. Ltd. (America) Inc. Electronic components Group 16 Collyer Quay #20-00 179 East Tasman Drive, Dornacher Stra§e 3 Hitachi Tower San Jose,CA 95134 D-85622 Feldkirchen, Munich Singapore 049318 Tel: <1> (408) 433-1990 Fax: <1>(408) 433-0223 Germany Tel: 535-2100 Tel: <49> (89) 9 9180-0

Fax: <49> (89) 9 29 30 00 Hitachi Europe Ltd. Electronic Components Group. Whitebrook Park Lower Cookham Road Maidenhead Berkshire SL6 8YA, United Kingdom Tel: <44> (1628) 585000 Fax: <44> (1628) 778322

Fax: 535-1533

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Hitachi Asia Ltd. Taipei Branch Office 3F, Hung Kuo Building. No.167, Tun-Hwa North Road, Taipei (105) Tel: <886> (2) 2718-3666 Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd. Group III (Electronic Components) 7/F., North Tower, World Finance Centre, Harbour City, Canton Road, Tsim Sha Tsui, Kowloon, Hong Kong Tel: <852> (2) 735 9218 Fax: <852> (2) 730 0281 Telex: 40815 HITEC HX

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